

SPECIFICATION OF LED CHIP

C630-55NN

[RED]

1) Commodity Type and Physical Characteristics.

1. Material InGaAlP/GaAs
2. Electrode

Top Side	P (anode) side	:Au Alloy/Al or Au Pad
Bottom Side	N (cathode) side	:Au Alloy
3. Electrode Pattern Fig.1
4. Chip Size Fig.2
5. Chip Thickness Fig.2
6. Emission Area Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Type	Max.	Unit
Forward Voltage	V _f	I _f =20mA		1.90	2.20	V
Forward Voltage	V _f	I _f =500mA		3.00	4.50	V
Reverse Current	I _r	V _r =5V			10	uA
Brightness	I _v	I _f =20mA	70	120		mcd
Power Intensity	P _o	I _f =20mA	0.8	1.4		mW
Peak Wavelength	λ _P	I _f =20mA	625	635	645	nm
Spectral Bandwidth	Δλ	I _f =20mA		15		nm
Rise Time	t _r	I _f =20mA		100		ns
Fall Time	t _f	I _f =20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

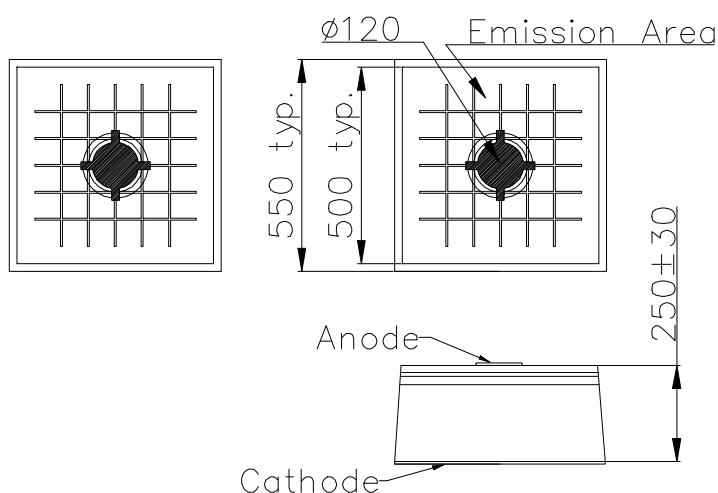


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area